MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM6J507NU

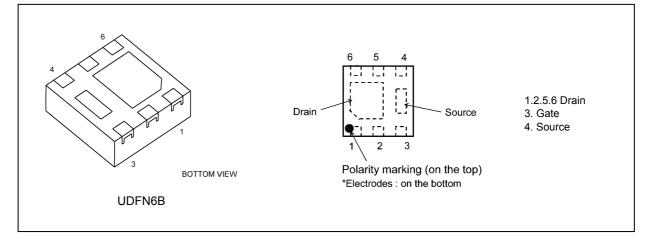
#### 1. Applications

Power Management Switches

#### 2. Features

- (1) 4 V gate drive voltage.
- (2) Low drain-source on-resistance
  - $\begin{array}{l} : {\rm R}_{\rm DS(ON)} = 20 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -10 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 28 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -4.5 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 32 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = -4.0 \ {\rm V}) \end{array}$

#### 3. Packaging and Pin Assignment



### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				V <sub>DSS</sub>	-30	V
Gate-source voltage				V <sub>GSS</sub>	-25 / +20	
Drain current (DC)			(Note 1)	Ι <sub>D</sub>	-10	A
Drain current (pulsed)			(Note 1), (Note 2)	I <sub>DP</sub>	-30	
Power dissipation			(Note 3)	PD	1.25	w
Power dissipation		(t ≤ 10 s)	(Note 3)	PD	2.5	W
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Repetitive rating; pulse width limited by maximum channel temperature.

- Note 3: Device mounted on a FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 645 mm<sup>2</sup>)
- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}$ = ±16 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V			-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D$ = -250 $\mu$ A, V <sub>GS</sub> = 0 V	-30	—	—	V
Gate threshold voltage	(Note 1)	V <sub>th</sub>	$V_{DS}$ = $V_{GS}$ , $I_D$ = -250 $\mu$ A	-1.0	_	-2.2	
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -4.0 A, V <sub>GS</sub> = -10 V	_	14	20	mΩ
			$I_D$ = -4.0 A, $V_{GS}$ = -4.5 V	_	19	28	
			I <sub>D</sub> = -4.0 A, V <sub>GS</sub> = -4.0 V	_	21	32	
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -2.0 A	_	14	_	S

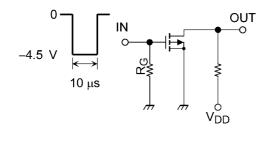
Note 1: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-250  $\mu$ A for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 2: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = -15 V, $V_{GS}$ = 0 V,	_	1150	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	185	—	
Output capacitance	C <sub>oss</sub>		_	210	_	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -15 V, I <sub>D</sub> = -2.0 A V <sub>GS</sub> = 0 to -4.5 V, R <sub>G</sub> = 10 Ω,	_	55	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$\begin{array}{l} Duty \leq 1\%, V_{IN} \text{: } t_r,  t_f < 5  \text{ns}, \\ \text{Common source, See Chapter 5.3.} \end{array}$	_	170	_	

### 5.3. Switching Time Test Circuit



 $\begin{array}{c} 0 \\ -4.5 \\ V \\ V_{DS(ON)} \\ V_{DD} \\ \end{array}$ 

Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

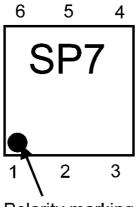
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = -15 V, V <sub>GS</sub> = -4.5 V,	—	13.6	20.4	nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = -10 A	_	2.6	_	
Gate-drain charge	Q <sub>gd</sub>			5.8		

### 5.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (N	Note 1)	$V_{\text{DSF}}$	I <sub>D</sub> = 4 A, V <sub>GS</sub> = 0 V	_	0.78	1.0	V

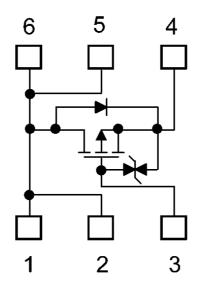
Note 1: Pulse measurement.

### 6. Marking

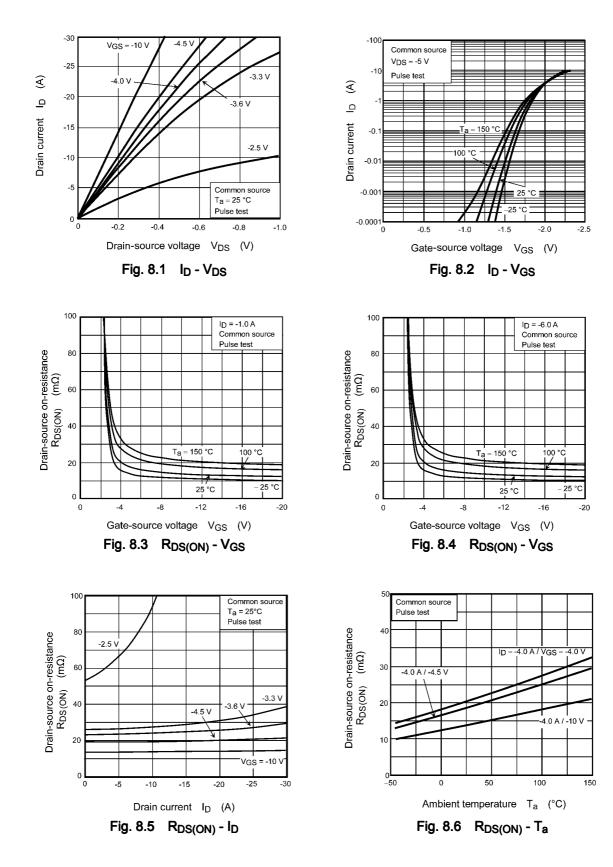


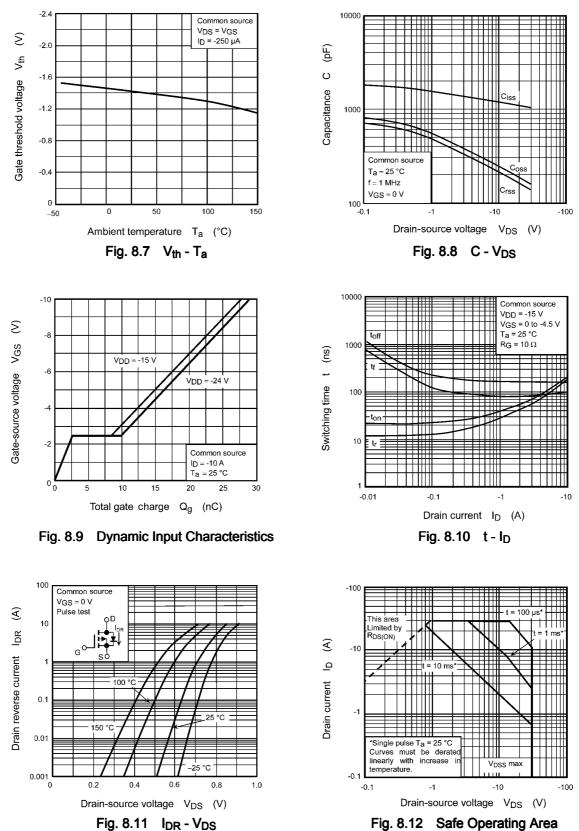
Polarity marking

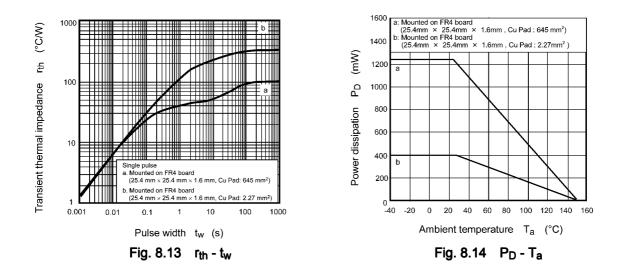
7. Internal Equivalent Circuit



#### 8. Characteristics Curves (Note)



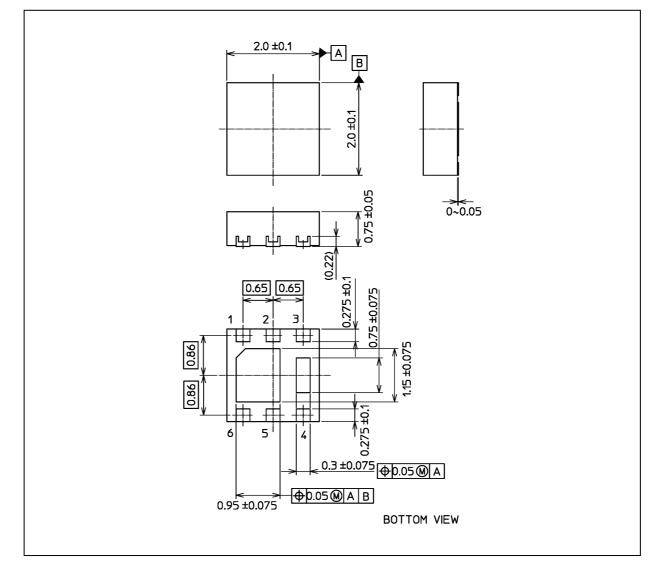




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### Package Dimensions

Unit: mm



Weight: 8.5 mg (typ.)

	Package Name(s)
TOSHIBA: 2-2AA1A	
Nickname: UDFN6B	
Nickhame. ODI NOB	

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